

N-Channel 30V (D-S) MOSFET

PRODUCT SUMMARY		
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)
30	0.021 at V _{GS} = 10 V	12 ^a
	0.033 at V _{GS} = 4.5 V	6

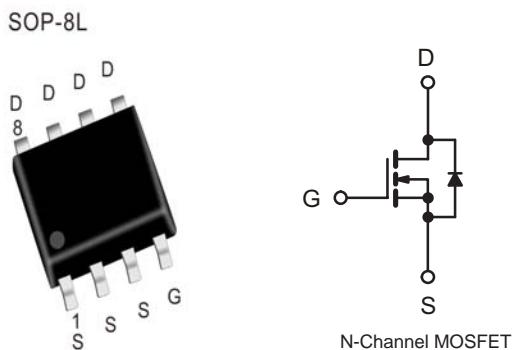
Features

- Low Gate Charge
- RoHS Compliant

Applications

- Notebook System Power
- Low Current DC/DC

Pin Configuration



Packing Information

Device	Marking	Reel Size	Tape Width	Quantity
EC4178	13D XXX	12"	13mm	3000pcs

Absolute Maximum Ratings (T_J=25 °C Unless Otherwise Noted)

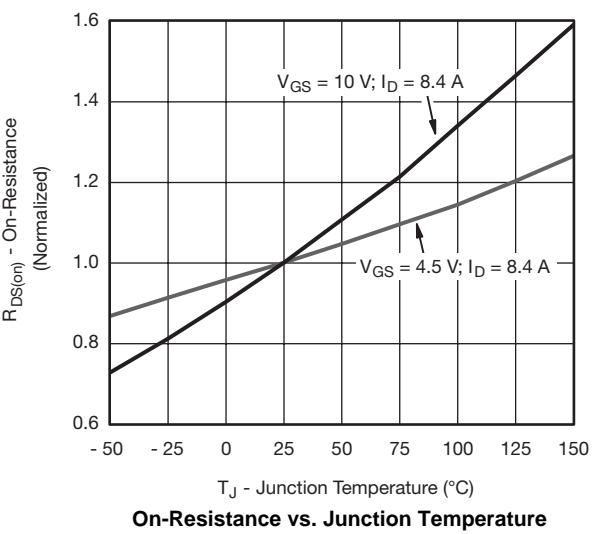
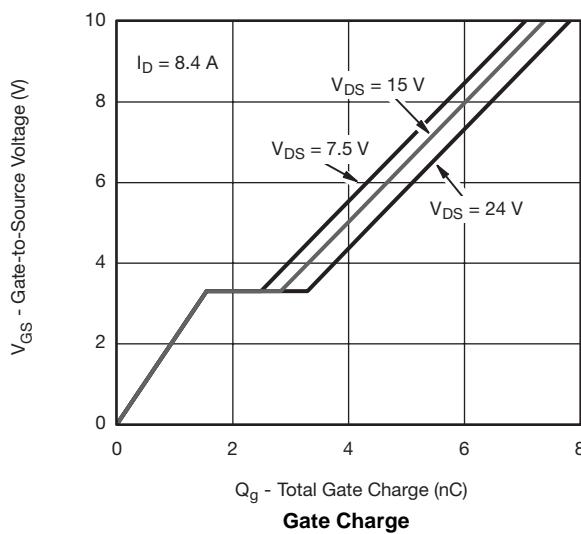
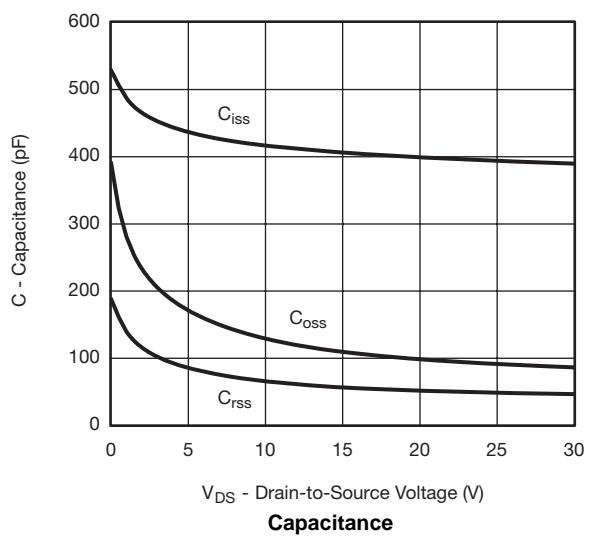
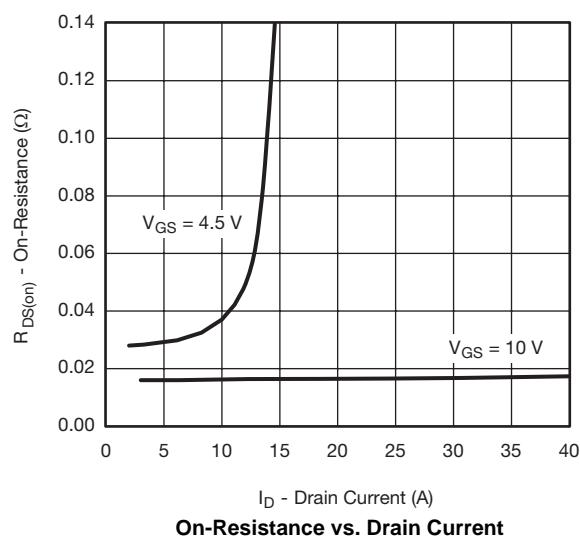
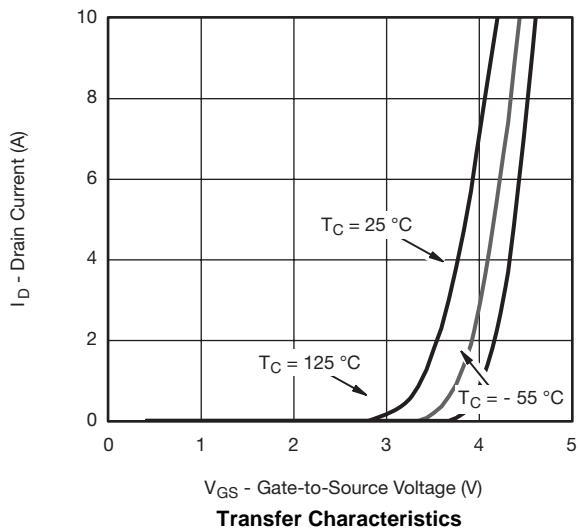
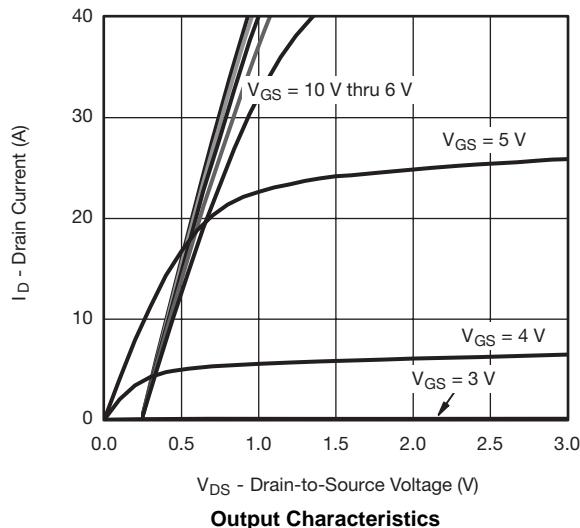
Symbol	Parameter	Value	Unit
P-MOSFET			
V _{DS}	Drain-Source Voltage	30	V
V _{GS}	Gate-Source Voltage	±25	V
I _D	Continuous Drain Current	12	A
I _{DM}	Pulse Drain Current	40	A
P _D	Maximum Power Dissipation	5	W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C
T _L	Lead Temperature for Soldering Purposes(1/8" from case for 10 s)	260	°C
Thermal Resistance Ratings			
R _{thJA}	Maximum Junction-to-Ambient t ≤ 10 s	53	°C/W
R _{thJF}	Maximum Junction-to-Foot (Drain) Steady State	25	°C/W

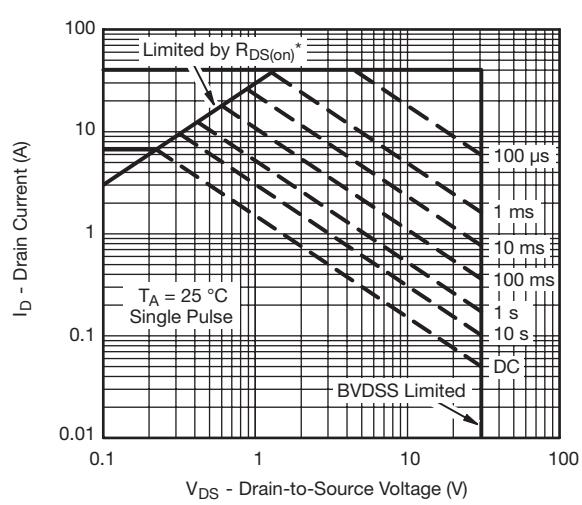
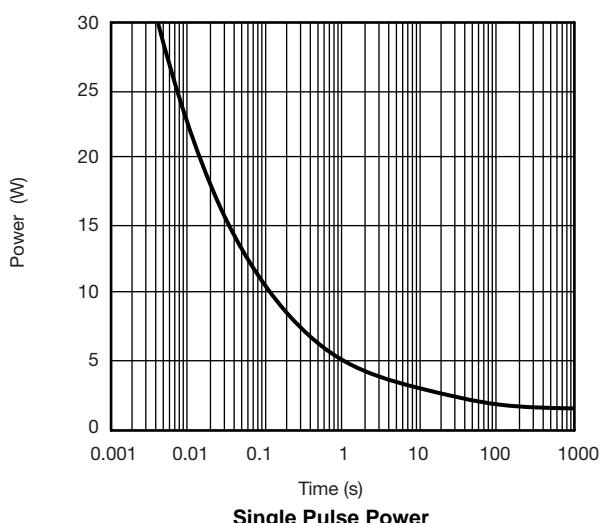
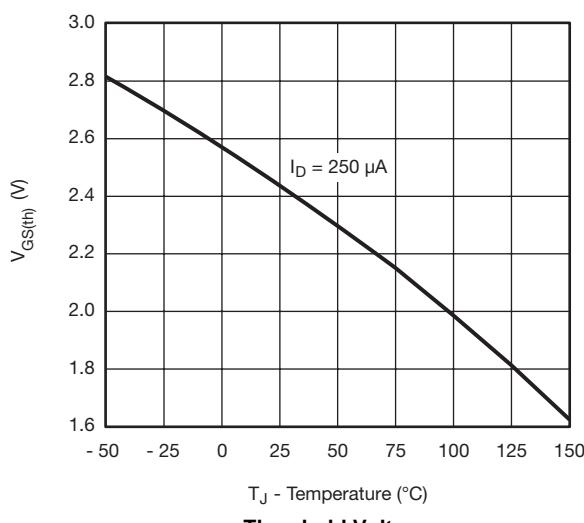
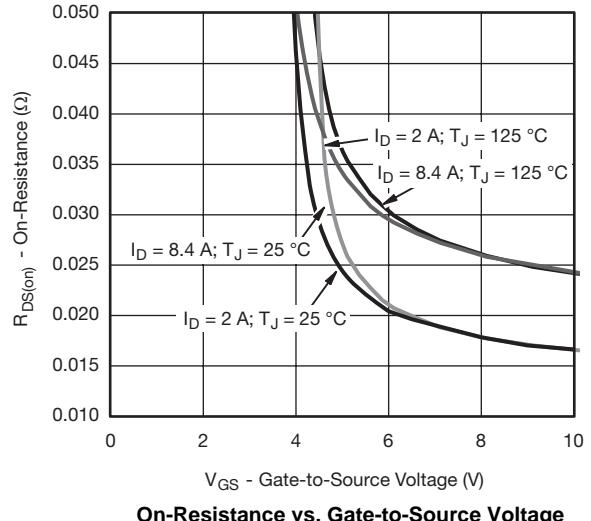
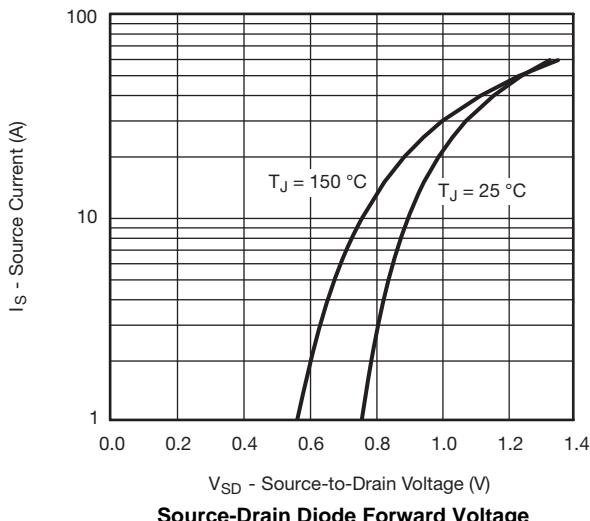
Notes:

- a. Package Limited.
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 10 s.
- d. Maximum under Steady State conditions is 85 °C/W.

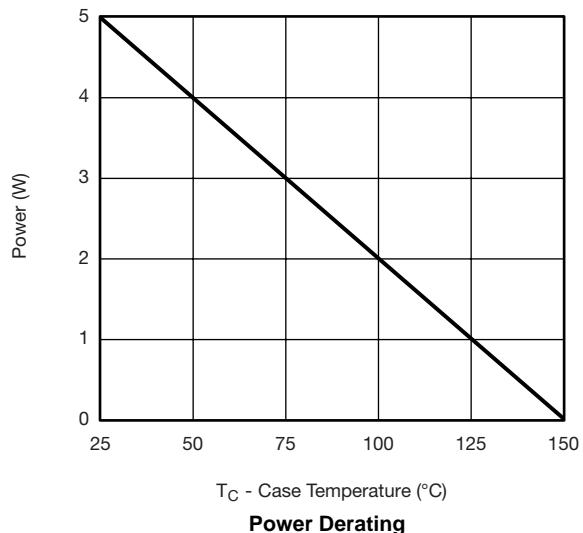
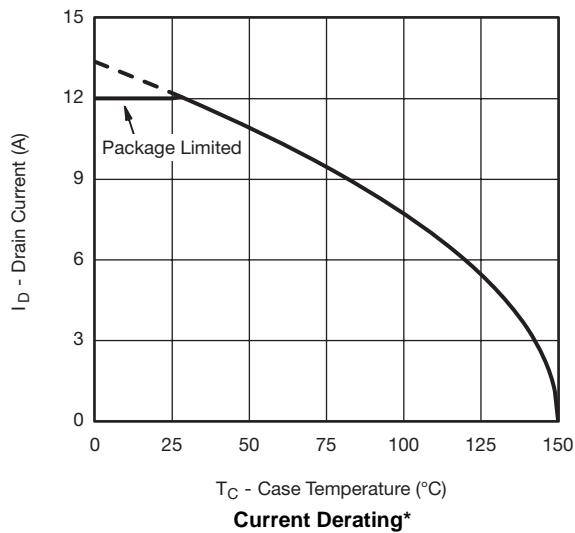
Electrical Characteristics ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
STATIC PARAMETERS						
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{GS} = 0\text{V}, I_D = 250 \mu\text{A}$	30			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 30\text{V}, V_{GS} = 0\text{V}$			1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 25\text{V}, V_{DS} = 0\text{V}$			± 100	nA
Gate threshold voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	1.4		2.8	V
Drain-source on-resistance(note1)	$R_{DS(\text{on})}$	$V_{GS} = 10\text{V}, I_D = -8.4\text{A}$		17	21	$\text{m}\Omega$
		$V_{GS} = 4.5\text{V}, I_D = 2\text{A}$		27	33	$\text{m}\Omega$
Forward transconductance(note1)	g_{FS}	$V_{DS} = 15\text{V}, I_D = 8.4\text{A}$		22		S
Diode forward voltage(note1)	V_{SD}	$I_S = 6.7\text{A}, V_{GS} = 0\text{V}$		0.85	1.2	V
DYNAMIC						
Input capacitance	C_{iss}	$V_{DS} = 15\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$		405		pF
Output capacitance	C_{oss}			110		pF
Reverse transfer capacitance	C_{rss}			56		pF
SWITCHING PARAMETERS (note 2)						
Turn-on delay time	$t_{d(on)}$	$V_{GS} = 4.5\text{V}, V_{DD} = 15\text{V}, R_L = 2.2\Omega, R_G = 1\Omega, I_D = 6.7\text{A}$		20	30	ns
Turn-on rise time	t_r			15	25	ns
Turn-off delay time	$t_{d(off)}$			11	20	ns
Turn-off fall time	t_f			10	15	ns
Total Gate Charge	Q_g	$V_{DS} = 15\text{V}, V_{GS} = 4.5\text{V}, I_D = 8.4\text{A}$		3.7	5.6	nC
Gate-Source Charge	Q_{gs}			1.6		nC
Gate-Drain Charge	Q_{gd}			1.3		nC

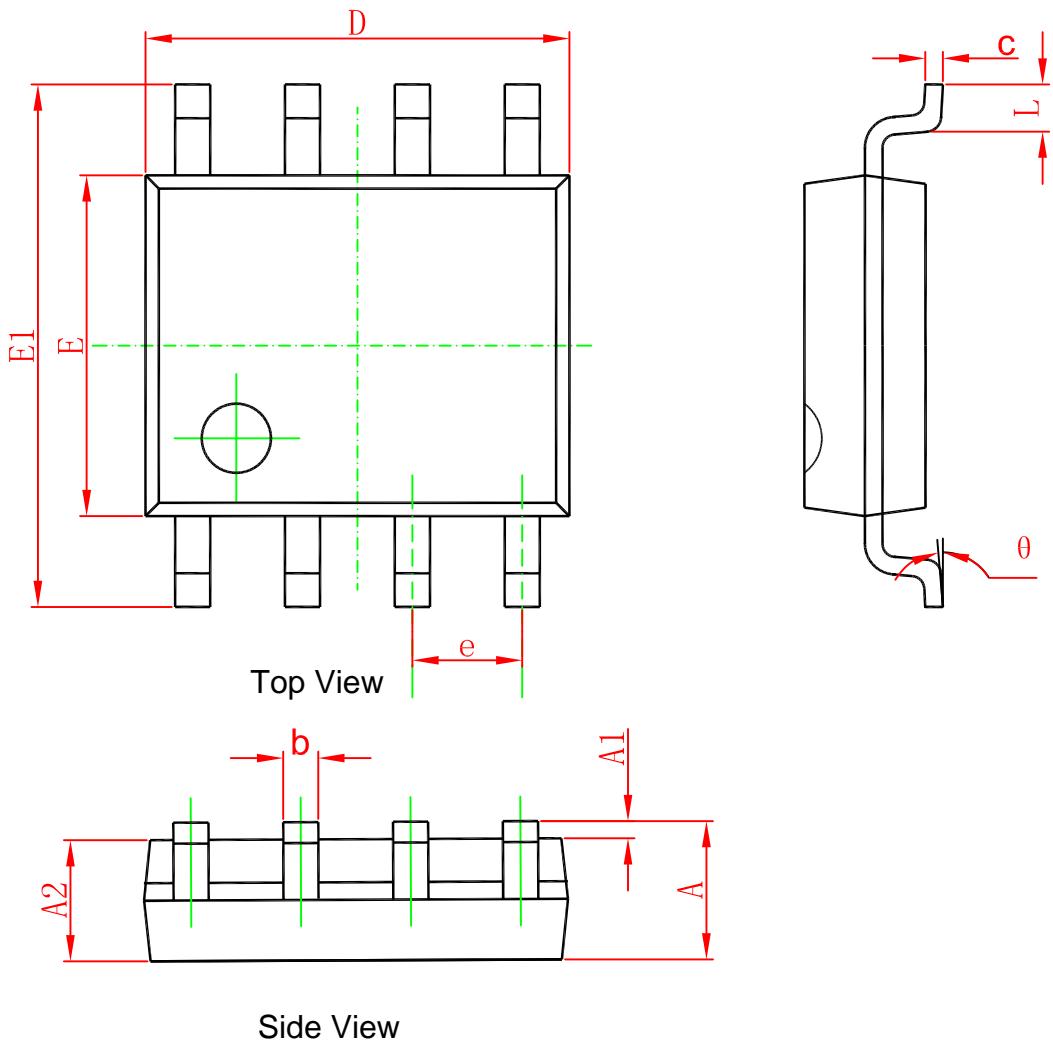
MOSFET TYPICAL CHARACTERISTICS (25°C, unless otherwise noted)


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* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

MOSFET TYPICAL CHARACTERISTICS (25°C, unless otherwise noted)

SOP-8L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°